

NSBC114YPDP6T5G

NSBC114YPDP6T5G Information

www.netvener.com	 NSBC114YPDP6T5G ON Semiconductor Discrete Semiconductor Products Transistors - Bipolar (BJT) - Arrays, Pre-Biased TRANS NPN/PNP PREBIAS SOT963 SOT-963 For the pricing/inventory/lead time, please contact	
For Reference Only	us Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

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NSBC114YPDP6T5G Specifications

Manufacturer Part Number NSBC114YPDP6T5G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - Bipolar (BJT) - Arrays, Pre-Biased Transistors - Bipolar (BJT) - Arrays, Pre-Biased Package SOT-963 Series - Transistor Type 1 NPN, 1 PNP - Pre-Biased (Dual) Current - Collector (Lc) (Max) 100mA Voltage - Collector Emitter Breakdown (Max) 50V Resistor - Base (R1) (Ohms) 10k Resistor - Emitter Base (R2) (Ohms) 47k DC Current Gain (hFE) (Min) @ Lc, Vce 80 @ 5mA, 10V Vec Saturation (Max) @ Ib, Lc 500nA Current - Collector Cutoff (Max) 500nA Frequency - Transition - Prequency - Transition - Power - Max 339mW Mounting Type SOT-963 Supplicr Device Package SOT-963		
CategoryDiscrete Semiconductor Products Transistors - Bipolar (BJT) - Arrays, Pre-BiasedPackageSOT-963Series-Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Lo) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)10kResistor - Emitter Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Lc, Vce80 @ 5mA, 10VVes Saturation (Max) @ Jb, Lc500nACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Manufacturer Part Number	NSBC114YPDP6T5G
IntegryTransistors - Bipolar (BJT) - Arrays, Pre-BiasedPackageSOT-963Series-Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Lc) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)10kResistor - Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Lc, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Lc250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Manufacturer	ON Semiconductor
PackageSOT-963Series-Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Ic) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)10kResistor - Base (R2) (Ohms)47kDC Current Gain (hFE) (Min @ Ic, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Category	Discrete Semiconductor Products
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Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Lo (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)10kResistor - Emitter Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Lc, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Lc250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Package	SOT-963
Current - Collector (Ic) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)10kResistor - Emitter Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Ic, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Series	-
Voltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)10kResistor - Emitter Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Ic, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max33mWMounting TypeSurface MountPackage / CaseS0T-963Supplier Device PackageS0T-963	Transistor Type	1 NPN, 1 PNP - Pre-Biased (Dual)
Resistor - Base (R1) (Ohms)10kResistor - Emitter Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Ic, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Current - Collector (Ic) (Max)	100mA
Resistor - Emitter Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Ic, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Voltage - Collector Emitter Breakdown (Max)	50V
DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Resistor - Base (R1) (Ohms)	10k
Vce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Resistor - Emitter Base (R2) (Ohms)	47k
Current - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	DC Current Gain (hFE) (Min) @ Ic, Vce	80 @ 5mA, 10V
Frequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Vce Saturation (Max) @ Ib, Ic	250mV @ 300µA, 10mA
Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Current - Collector Cutoff (Max)	500nA
Mounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Frequency - Transition	_
Package / CaseSOT-963Supplier Device PackageSOT-963	Power - Max	339mW
Supplier Device Package SOT-963	Mounting Type	Surface Mount
	Package / Case	SOT-963
Report errors?	Supplier Device Package	SOT-963
		Report errors?

NSBC114YPDP6T5G Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE BUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

NSBC114YPDP6T5G Payment Methods



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